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Is Now

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Preferred Device

Silicon Tuning Diode

These devices are designed in the popular Plastic Surface Mount Package for high volume requirements of FM Radio and TV tuning and AFC, general frequency control and tuning applications. They provide solid–state reliability in replacement of mechanical tuning methods.

Features

- High Q
- Controlled and Uniform Tuning Ratio
- Standard Capacitance Tolerance 10%
- Complete Typical Design Curves
- Pb–Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Continuous Reverse Voltage	V _R	30	Vdc	
Peak Forward Current	١ _F	200	mAdc	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, $T_A = 25^{\circ}C$ (Note 1) Derate above $25^{\circ}C$	P _D	200 1.57	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T _J , T _{stg}	150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 Minimum Pad



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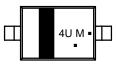
30 VOLT VOLTAGE VARIABLE CAPACITANCE DIODE

1 0-2 CATHODE ANODE



PLASTIC SOD-323 CASE 477 STYLE 1

MARKING DIAGRAM



4U = Device Code

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMVL2105T1	SOD-323	3000 / Tape & Reel
MMVL2105T1G	SOD-323 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit
Reverse Breakdown Voltage $(I_R = 10 \ \mu Adc)$	V _{(BR)R}	30	-	-	Vdc
Reverse Voltage Leakage Current ($V_R = 25 Vdc, T_A = 25^{\circ}C$)	I _R	-	-	0.1	μAdc
Diode Capacitance Temperature Coefficient $(V_R = 4.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	TC _C	-	280	-	ppm/°C

	C _T , Diode Capacitance V _R = 4.0 Vdc, f = 1.0 MHz pF		Q, Figure of Merit V _R = 4.0 Vdc, f = 50 MHz	TR, Tuning Ratio C ₂ /C ₃₀ f = 1.0 MHz			
Device	Min	Nom	Max	Тур	Min	Тур	Max
MMVL2105T1	13.5	15	16.5	400	2.5	2.9	3.2

PARAMETER TEST METHODS

1. C_T, DIODE CAPACITANCE

 $(C_T = C_C + C_J)$. C_T is measured at 1.0 MHz using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

2. TR, TUNING RATIO

TR is the ratio of C_{T} measured at 2.0 Vdc divided by C_{T} measured at 30 Vdc.

3. Q, FIGURE OF MERIT

Q is calculated by taking the G and C readings of an admittance bridge at the specified frequency and substituting in the following equations:

$$Q = \frac{2\pi fC}{G}$$

(Boonton Electronics Model 33AS8 or equivalent). Use Lead Length $\approx 1/16$ ".

4. TC_C, DIODE CAPACITANCE TEMPERATURE COEFFICIENT

TC_C is guaranteed by comparing C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = -65°C with C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = +85°C in the following equation, which defines TC_C:

$$\mathsf{TC}_{\mathsf{C}} = \left| \frac{\mathsf{C}_{\mathsf{T}}(+\ 85^{\circ}\mathsf{C}) - \mathsf{C}_{\mathsf{T}}(-65^{\circ}\mathsf{C})}{85 + 65} \right| \cdot \frac{10^6}{\mathsf{C}_{\mathsf{T}}(25^{\circ}\mathsf{C})}$$

Accuracy limited by measurement of C_T to ± 0.1 pF.

TYPICAL DEVICE CHARACTERISTICS

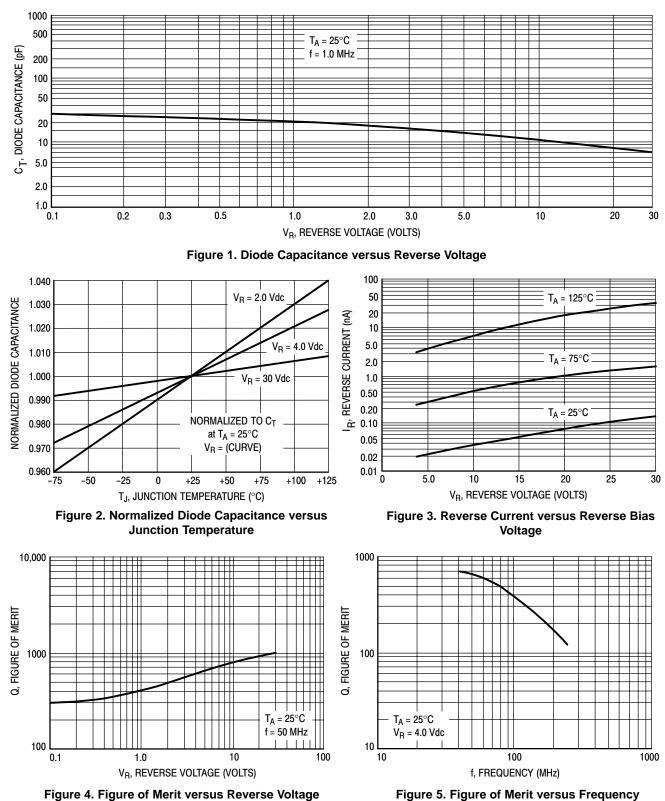
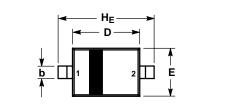
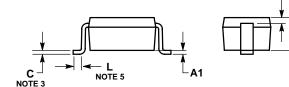


Figure 5. Figure of Merit versus Frequency

PACKAGE DIMENSIONS

SOD-323 CASE 477-02 ISSUE G





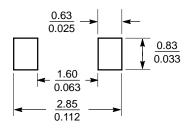
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MIL	LIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.031	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A3	0.15 REF			0.006 REF			
b	0.25	0.32	0.4	0.010	0.012	0.016	
С	0.089	0.12	0.177	0.003	0.005	0.007	
D	1.60	1.70	1.80	0.062	0.066	0.070	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
L	0.08			0.003			
HE	2.30	2.50	2.70	0.090	0.098	0.105	

STYLE 1: PIN 1. CATHODE 2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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